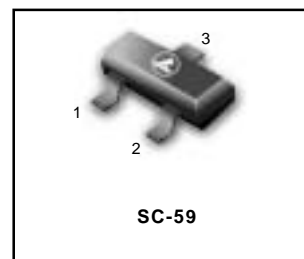


SCHOTTKY BARRIER DIODE

LRB491T1

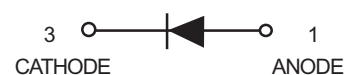
FEATURE

- Silicon epitaxial planar.
- Small plastic SMD package.
- High current capacity($I_F=1.0A$).
- Ultra low V_F . ($V_F=0.40V$ Typ. at 1A)
- For switching power supply Applications.
- Pb-Free Package is available.



DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LRB491T1	10T	3000/Tape&Reel
LRB491T1G	10T (Pb-Free)	3000/Tape&Reel



MAXIMUM RATINGS($T_a=25^{\circ}C$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	25	V
DC reverse voltage	V_R	20	V
DC forward current	I_F	1.0	A
Peak forward surge current *	I_{FSM}	3	A
Junction temperature	T_j	125	$^{\circ}C$
Storage temperature	T_{stg}	-40~+125	$^{\circ}C$

* 60Hz for 1 μ s

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.45	V	$I_F=1.0A$
Reverse current	I_R	-	-	200	μA	$V_R=20V$

Note) ESD sensitive product handling required.

LRB491T1

ELECTRICAL CHARACTERISTIC CURVES(Ta=25°C)

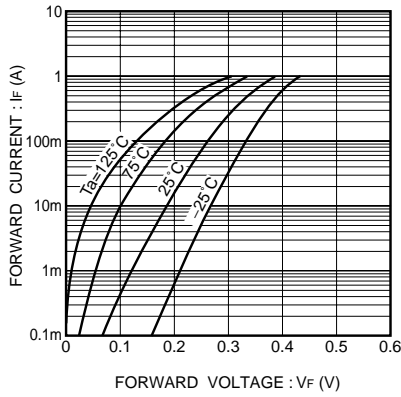


Fig.1 Forward characteristics

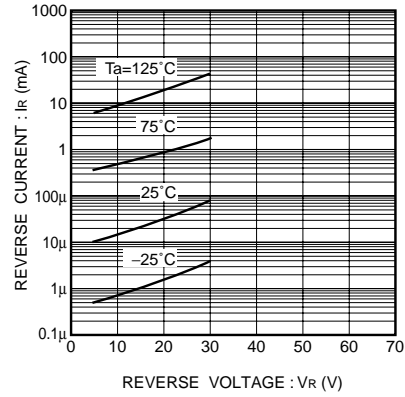


Fig.2 Reverse characteristics

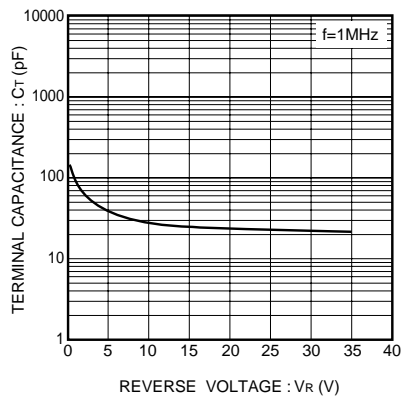


Fig.3 Capacitance between terminals characteristics

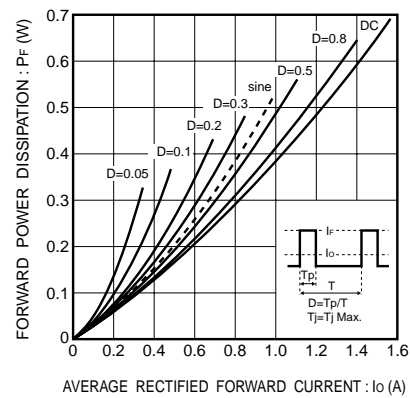


Fig.4 Forward power dissipation characteristics

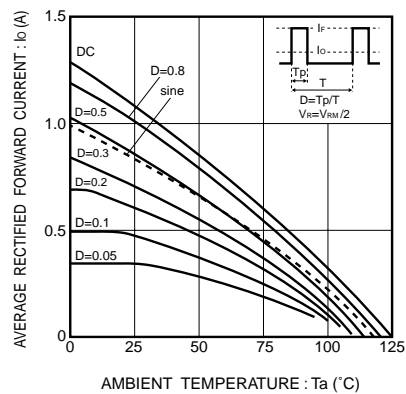
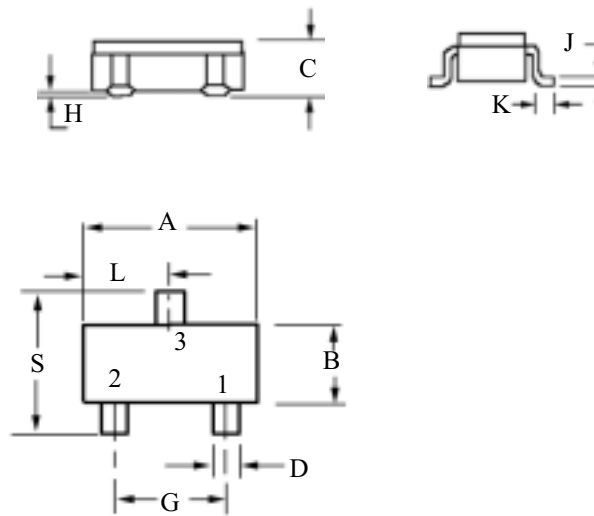


Fig.5 Derating curve ($I_o - T_a$)

LRB491T1
SC-59


DIN	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.70	3.10	0.1063	0.1220
B	1.3	1.70	0.0512	0.0669
C	1.00	1.30	0.0394	0.0511
D	0.35	0.50	0.0138	0.0196
G	1.70	2.10	0.0670	0.0826
H	0.0130	0.100	0.0005	0.00040
J	0.1	0.26	0.0040	0.0102
K	0.20	0.60	0.0079	0.0236
L	1.25	1.65	0.0493	0.0649
S	2.50	3.00	0.0985	0.1181